

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: Appl. No. GR 98 P 2499	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Applicant THOMAS HANEDER ET AL.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Filing Date MARCH 7, 2001	Group Art Unit

J1046 U.S. PTO
09/07/2001
03/07/01

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
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	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
TL	J	0459773A2	12/91	Europe			X
TL	K	0716455A2	06/96	Europe			X
TL	L	0716455A3	06/96	Europe			X
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

TL.		"A Single-Transistor Ferroelectric Memory Cell", Takahashi Nakamura et al., XP 000557557, IEEE, ISSCC, 1995, Technology Directions, Display, Photonics and Ferroelectric Memo, pp. 68-69 and 340
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EXAMINER	<i>[Signature]</i>	DATE CONSIDERED	<i>9/9/02</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.